

REMARKS

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Respectfully submitted,



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Marked up copy of claims as amended:

Cancel Claims 1-11.

15.(Amended) The semiconductor device according to claim 12, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, [or] and a portable information terminal.

Cancel Claims 16-40.

Please add new claims 41-78 as follows.

--41.(New) The semiconductor device according to claim 12, wherein said gate electrode is located over said semiconductor layer.

42.(New) The semiconductor device according to claim 12, wherein said tungsten film has an electrical resistivity of $20 \mu\Omega \cdot \text{cm}$ or less.

43.(New) A semiconductor device comprising:
a semiconductor layer over a substrate; and
a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising nitride and a second conductive layer comprising tungsten on said first conductive layer.

44.(New) The semiconductor device according to claim 43, wherein said gate electrode is located over said semiconductor layer.

45.(New) The semiconductor device according to claim 43, wherein said tungsten film has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

46.(New) The semiconductor device according to claim 43, wherein said semiconductor device is an active matrix type liquid crystal display device.

47.(New) The semiconductor device according to claim 43, wherein said semiconductor device is an EL display device.

48.(New) The semiconductor device according to claim 43, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.

49.(New) A semiconductor device comprising:
a semiconductor layer over a substrate; and
a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising tungsten nitride and a second conductive layer comprising tungsten on said first conductive layer.

50.(New) The semiconductor device according to claim 49, wherein said gate electrode is located over said semiconductor layer.

51.(New) The semiconductor device according to claim 49, wherein said tungsten film has an electrical resistivity of $20 \mu\Omega\cdot\text{cm}$ or less.

52.(New) The semiconductor device according to claim 49, wherein said semiconductor device is an active matrix type liquid crystal display device.

53.(New) The semiconductor device according to claim 49, wherein said semiconductor device is an EL display device.

54.(New) The semiconductor device according to claim 49, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.

55.(New) A semiconductor device comprising:
a semiconductor layer over a substrate; and
a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising tungsten nitride which surrounds a second conductive layer comprising tungsten.

56.(New) The semiconductor device according to claim 55, wherein said gate electrode is located over said semiconductor layer.

57.(New) The semiconductor device according to claim 55, wherein said tungsten film has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

58.(New) The semiconductor device according to claim 55, wherein said semiconductor device is an active matrix type liquid crystal display device.

59.(New) The semiconductor device according to claim 55, wherein said semiconductor device is an EL display device.

60.(New) The semiconductor device according to claim 55, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.

61.(New) A semiconductor device comprising:

a semiconductor layer over a substrate; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising nitride and a second conductive layer comprising tungsten on said first conductive layer. and

wherein said first conductive layer has a taper angle of between 5 and 85°.

62.(New) The semiconductor device according to claim 61, wherein said gate electrode is located over said semiconductor layer.

63.(New) The semiconductor device according to claim 61, wherein said tungsten film has an electrical resistivity of 20 $\mu\Omega\cdot\text{cm}$ or less.

64.(New) The semiconductor device according to claim 61, wherein said semiconductor device is an active matrix type liquid crystal display device.

65.(New) The semiconductor device according to claim 61, wherein said semiconductor device is an EL display device.

66.(New) The semiconductor device according to claim 61, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.

67.(New) A semiconductor device comprising:

a semiconductor layer over a substrate; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising tungsten nitride and a second conductive layer comprising tungsten on said first conductive layer, and

wherein said first conductive layer has a taper angle of between 5 and 85°.

68.(New) The semiconductor device according to claim 67, wherein said gate electrode is located over said semiconductor layer.

69.(New) The semiconductor device according to claim 67, wherein said tungsten film has an electrical resistivity of 20 $\mu\Omega\cdot\text{cm}$ or less.

70.(New) The semiconductor device according to claim 67, wherein said semiconductor device is an active matrix type liquid crystal display device.

71.(New) The semiconductor device according to claim 67, wherein said semiconductor device is an EL display device.

72.(New) The semiconductor device according to claim 67, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.

73.(New) A semiconductor device comprising:

a semiconductor layer over a substrate; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising tungsten nitride which surrounds a second conductive layer comprising tungsten, and

wherein said first conductive layer has a taper angle of between 5 and 85°.

74.(New) The semiconductor device according to claim 73, wherein said gate electrode is located over said semiconductor layer.

75.(New) The semiconductor device according to claim 73, wherein said tungsten film has an electrical resistivity of 20 $\mu\Omega\cdot\text{cm}$ or less.

76.(New) The semiconductor device according to claim 73, wherein said semiconductor device is an active matrix type liquid crystal display device.

77.(New) The semiconductor device according to claim 73, wherein said semiconductor device is an EL display device.

78.(New) The semiconductor device according to claim 73, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.--